

THREE - PHASE SILICON BRIDGES

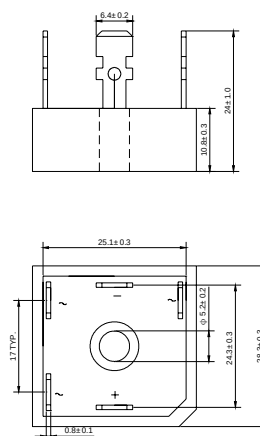
VOLTAGE RANGE: 1200 -- 1600 V

CURRENT: 25.0 A

FEATURES

- ◇ Rating to 1600 V
- ◇ Low forward voltage drop
- ◇ Small size, simple installation
- ◇ Tinned copper leads
- ◇ Mounting: Thru hole for #6 screw

DB25



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

		DB25 - 12	DB25 - 14	DB25 - 16	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	1200	1400	1600	V
Maximum RMS voltage	V_{RMS}	840	980	1120	V
Maximum DC blocking voltage	V_{DC}	1200	1400	1600	V
Maximum average forward rectified output current @ $T_A = 50^\circ\text{C}$	$I_{(AV)}$	25.0			A
Peak forward surge current 8.3ms single half-sine-wave	I_{FSM}	350.0			A
Maximum forward voltage drop per element at 8.0 A peak	V_F	1.05			V
Maximum reverse current @ $T_A = 25^\circ\text{C}$ at rated DC blocking voltage per element @ $T_A = 100^\circ\text{C}$	I_R	10 1.0			μA mA
Thermal resistance junction to case	$R_{\theta JC}$	2.4			K/W
Operating temperature range	T_j	- 55 --- + 125			$^\circ\text{C}$
Storage temperature range	T_{STG}	- 55 --- + 150			$^\circ\text{C}$

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